

## General Description

The WST2333B is the highest performance trench P-Ch MOSFET with extreme high cell density, which provide excellent  $R_{DS(on)}$  and gate charge for most of the small power switching and load switch applications.

The WST2333B meet the RoHS and Green Product requirement with full function reliability approved.

## Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent  $C_{dv}/dt$  effect decline
- Green Device Available

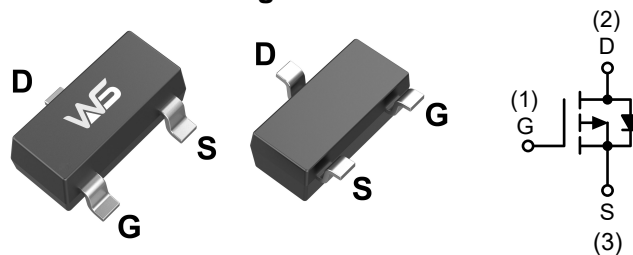
## Product Summary

$BV_{DSS}$	$R_{DS(on)}$	$I_D$
-15V	40m $\Omega$	-4.4A

## Applications

- High Frequency Point-of-Load Synchronous Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

## SOT-23L Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-15	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D@T_c=25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ -4.5V <sup>1</sup>	-4.4	A
$I_D@T_c=70^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ -4.5V <sup>1</sup>	-3.4	A
$I_{DM}$	Pulsed Drain Current	-24	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation <sup>3</sup>	1.4	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	---	125	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	80	$^\circ\text{C}/\text{W}$

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V$ , $I_D=-250\mu A$	-15	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-4.5V$ , $I_D=-4.1A$	---	40	48	$m\Omega$
		$V_{GS}=-2.5V$ , $I_D=-3A$	---	45	65	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_D=-250\mu A$	-0.45	-0.7	-1.2	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=-12V$ , $V_{GS}=0V$ , $T_J=25^\circ\text{C}$	---	---	-1	$\mu A$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 12V$ , $V_{DS}=0V$	---	---	$\pm 100$	nA
$Q_g$	Total Gate Charge	$V_{DS}=-4V$ , $I_D=-4.1A$ , $V_{GS}=-4.5V$	---	7.8	---	nC
$Q_{gs}$	Gate-Source Charge		---	1.2	---	
$Q_{gd}$	Gate-Drain Charge		---	1.6	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-4V$ , $I_D=-3.3A$ $R_L=1.2\Omega$ , $V_{GEN}=-4.5V$ , $R_g=1\Omega$	---	12	---	ns
$T_r$	Rise Time		---	35	---	
$T_{d(off)}$	Turn-Off Delay Time		---	10	---	
$T_f$	Fall Time		---	30	---	
$C_{iss}$	Input Capacitance	$V_{DS}=-4V$ , $V_{GS}=0V$ , $f=1.0\text{MHz}$	---	738	1500	pF
$C_{oss}$	Output Capacitance		---	280	---	
$C_{rss}$	Reverse Transfer Capacitance		---	190	---	

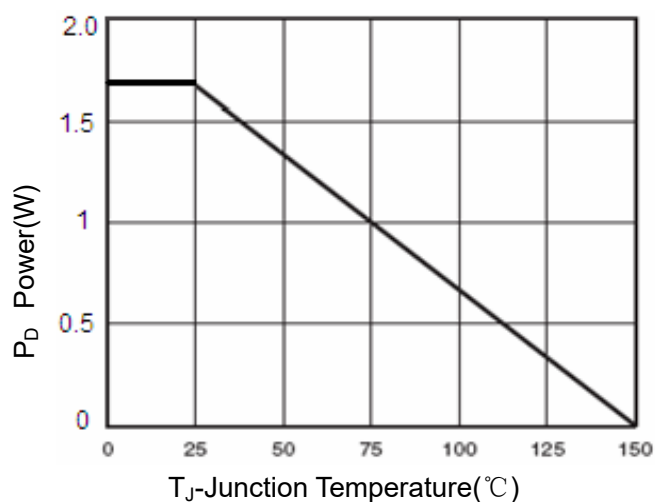
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current	$V_G=V_D=0V$ , Force Current	---	---	-4.1	A
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0V$ , $I_S=-1.6A$ , $T_J=25^\circ\text{C}$	---	---	-1.2	V

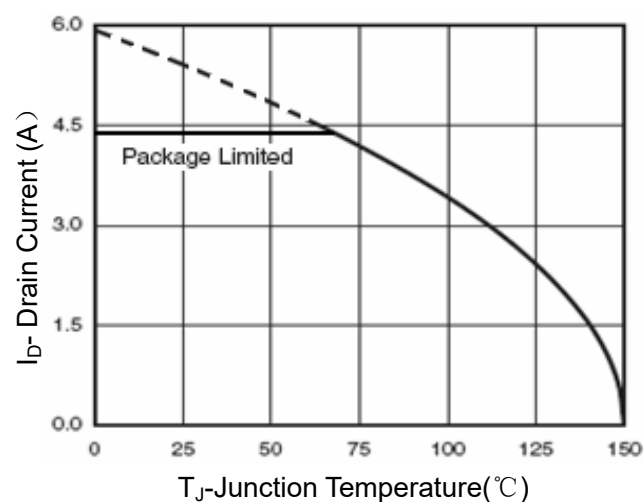
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

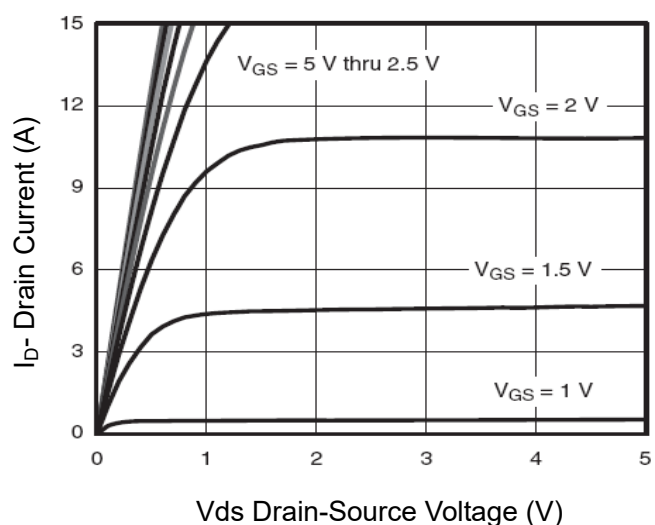
## Typical Characteristics



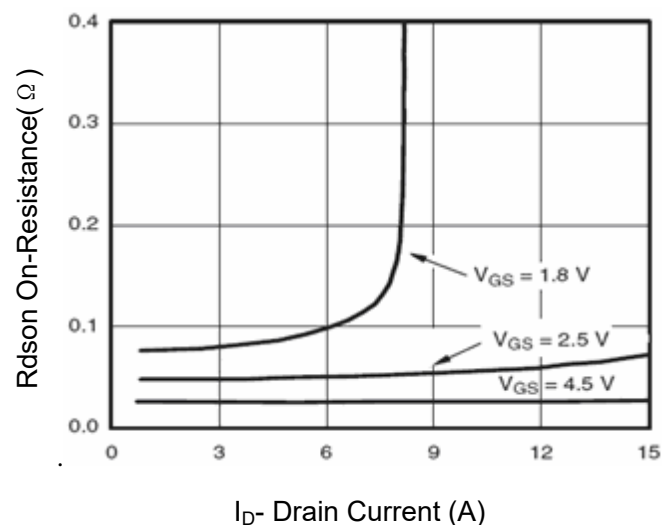
**Figure 3 Power Dissipation**



**Figure 4 Drain Current**



**Figure 5 Output Characteristics**



**Figure 6 Drain-Source On-Resistance**

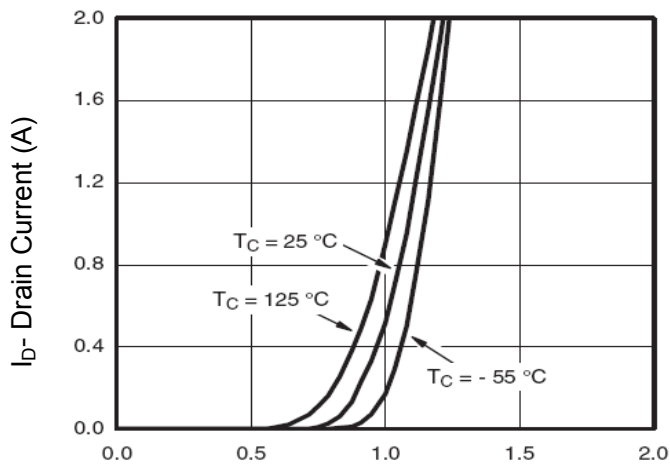


Figure 7 Transfer Characteristics

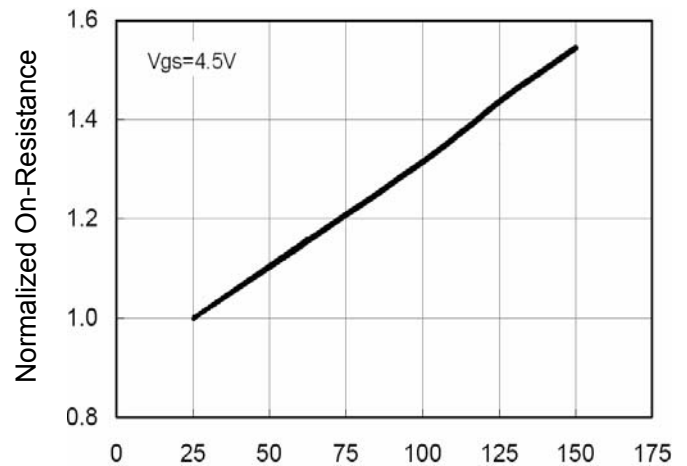


Figure 8 Drain-Source On-Resistance

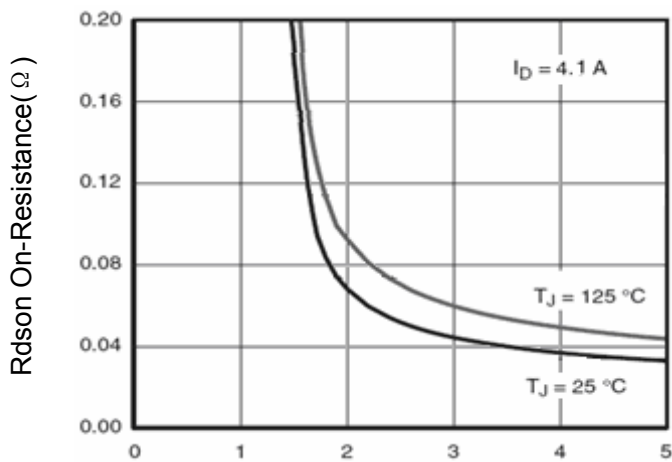


Figure 9  $R_{DS(on)}$  vs  $V_{GS}$

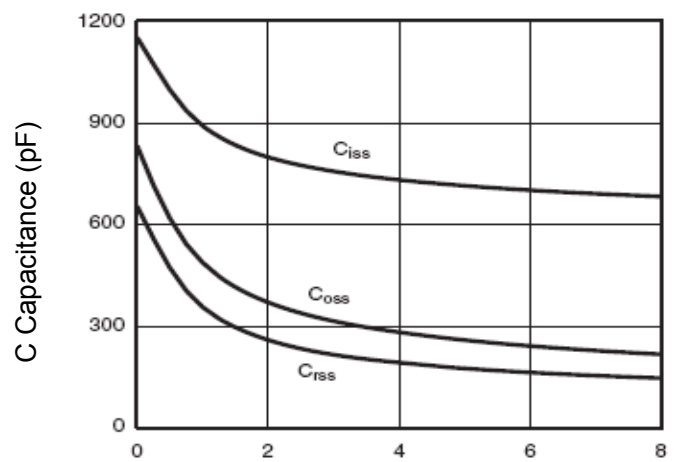


Figure 10 Capacitance vs  $V_{DS}$

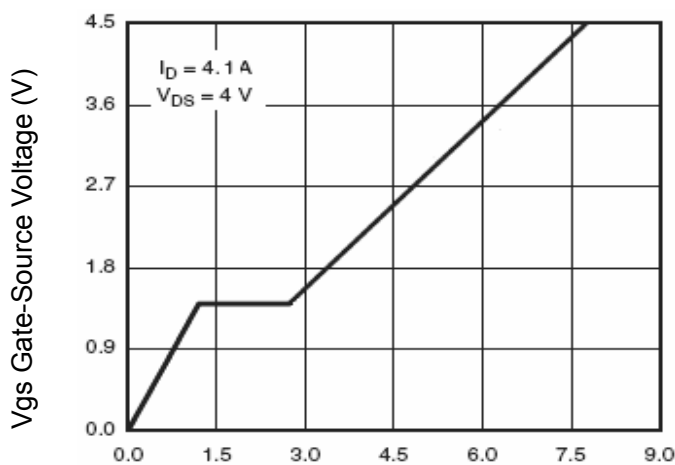


Figure 11 Gate Charge

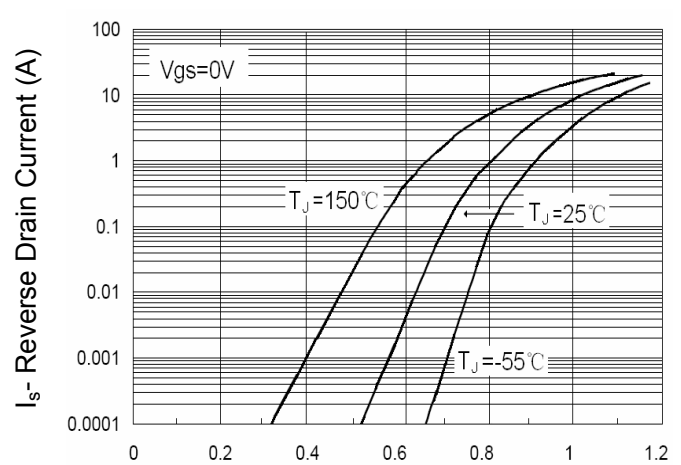
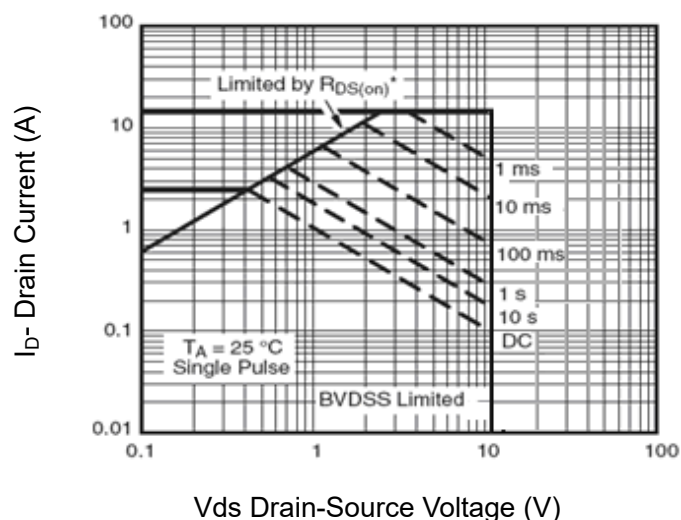
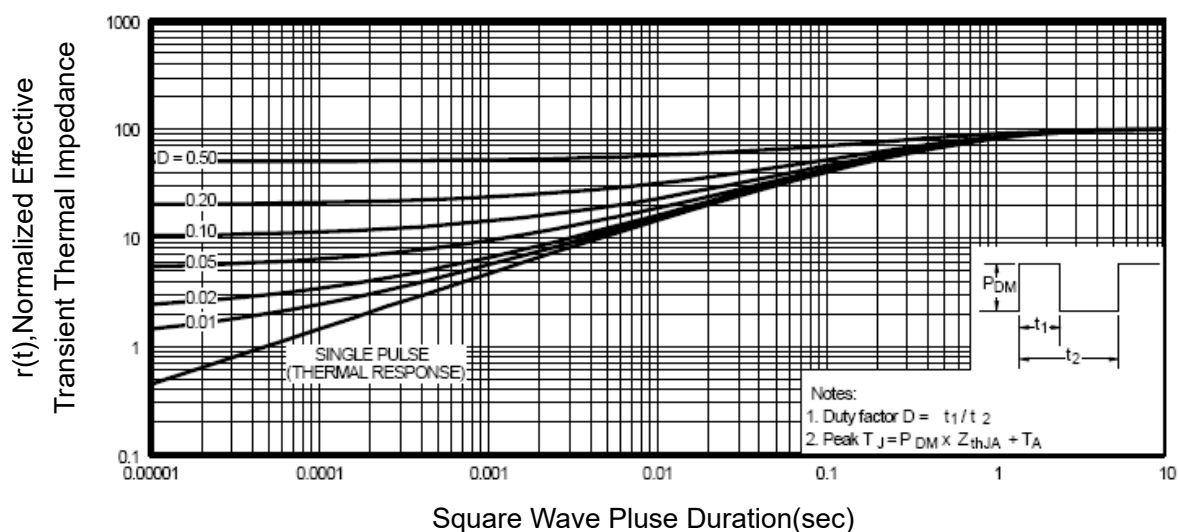


Figure 12 Source-Drain Diode Forward

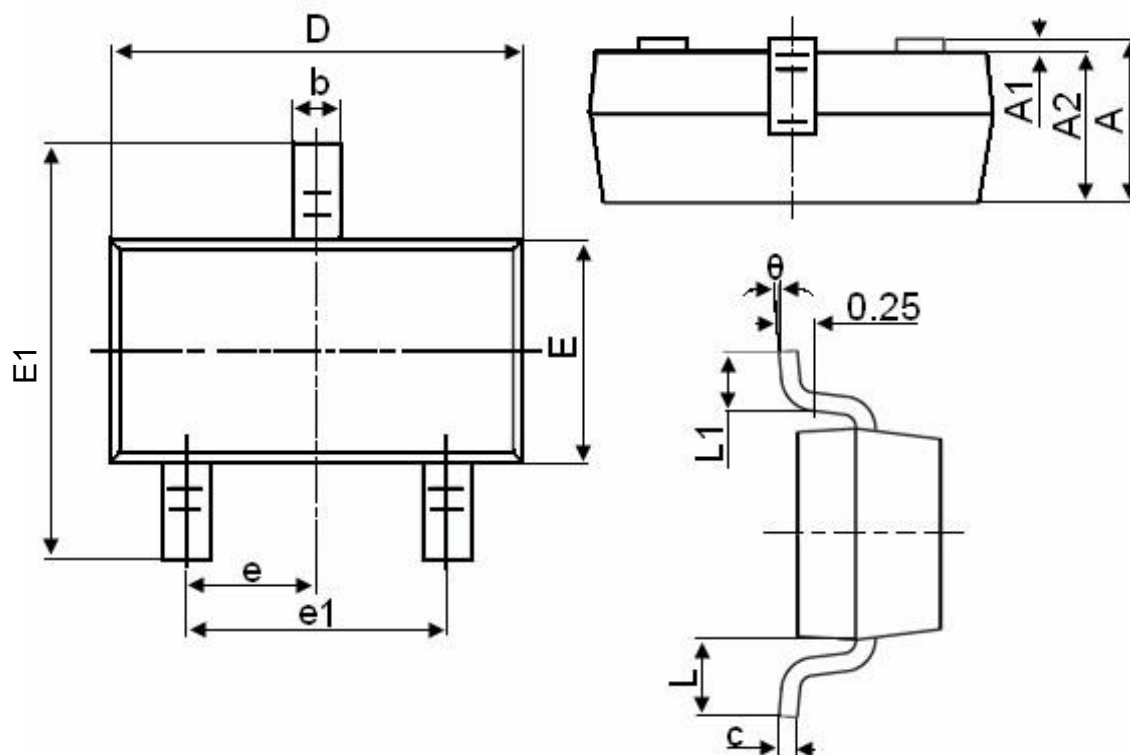


Vds Drain-Source Voltage (V)  
**Figure 13 Safe Operation Area**



**Figure 14 Normalized Maximum Transient Thermal Impedance**

## Packaging information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

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